

Amendments to show changes made
(Additions in bold, deletions in bold brackets)

Claims 1 and 7:

1. (Amended) A semiconductor bridge (SCB) device, comprising:

a laminate layer on top of an insulating material, wherein the laminate layer comprises a series of layers of at least two reactive materials, and wherein the laminate layer comprises, two relatively large sections that substantially cover the surface area of the insulating material, and

a bridge section joining the two relatively large sections;

for each of the two relatively large sections, at least one conductive contact pad coupled to at least one of the series of layers **of that relatively large section**, wherein a predetermined current **between [through the]** at least one conductive contact pad **on one of the relatively large sections and at least one conductive pad on the other of the relatively large sections** causes the bridge section to initiate a reaction in which the laminate layer is involved.

7. (Amended) The SCB device of claim 1, wherein the [at least one] conductive contact **pads** **comprise [pad comprises]** titanium, nickel and gold.